

BAS40HP

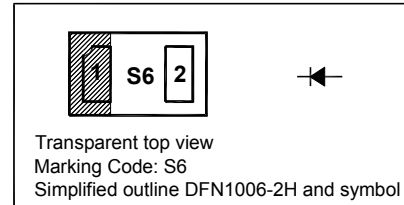
Silicon Epitaxial Planar Schottky Barrier Diode

Features

- Low forward voltage
- Fast switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	40	V
DC Blocking Voltage	V_R	40	V
Forward Continuous Current	I_F	200	mA
Peak Forward Surge Current (at $t_p = 8.3$ ms)	I_{FSM}	600	mA
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10 \mu\text{A}$	$V_{(BR)R}$	40	-	V
Forward Voltage at $I_F = 1$ mA at $I_F = 40$ mA	V_F V_F	- -	0.38 1	V V
Reverse Current at $V_R = 30$ V	I_R	-	200	nA
Reverse Recovery Time at $I_F = I_R = 10$ mA to $I_R = 1$ mA, $R_L = 100 \Omega$	t_{rr}	-	5	ns
Capacitance at $V_R = 0$ V, $f = 1$ MHz	C_j	-	5	pF

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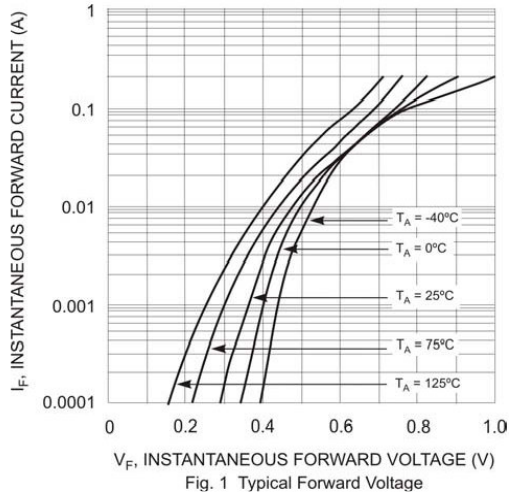


Fig. 1 Typical Forward Voltage

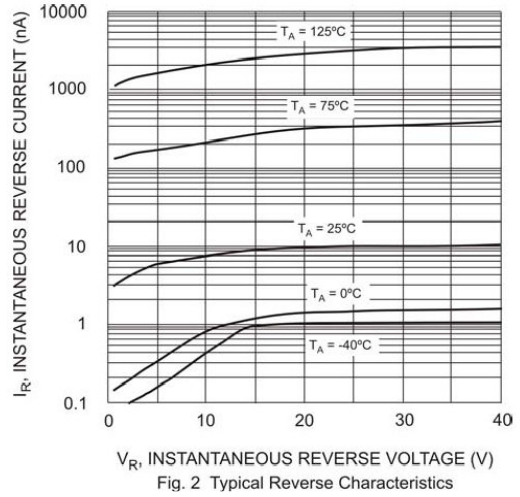


Fig. 2 Typical Reverse Characteristics

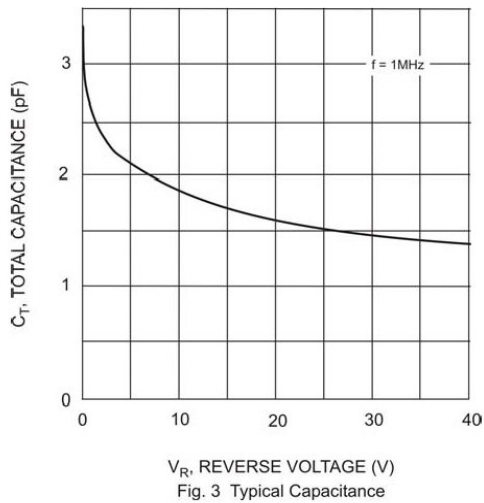


Fig. 3 Typical Capacitance

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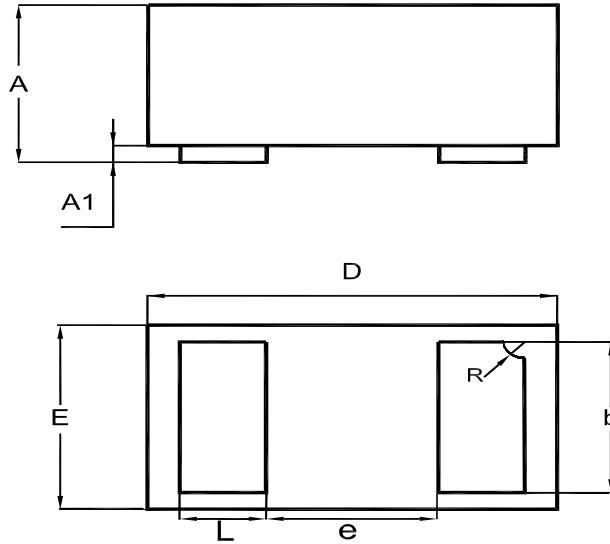
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PACKAGE OUTLINE

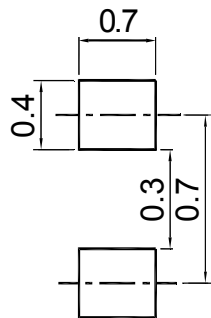
Plastic surface mounted package

DFN1006-2H



UNIT	A	A1	b	D	E	e	L	R
mm	0.51 0.46	0.05 0	0.55 0.45	1.05 0.95	0.65 0.55	0.4	0.3 0.2	0.15 0.05

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN1006-2H	8	4 ± 0.1	0.157 ± 0.004	178	7	5,000

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